

FIG.1

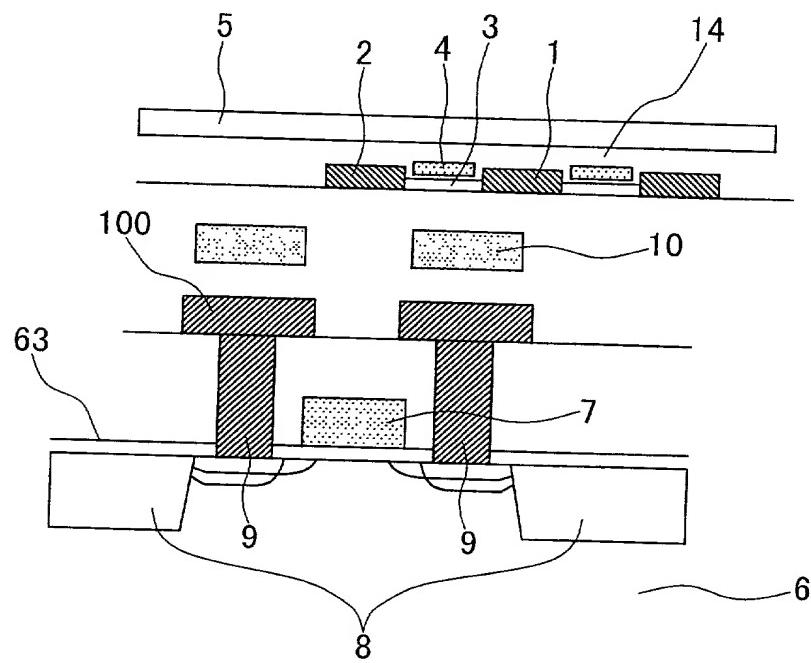


FIG.2a

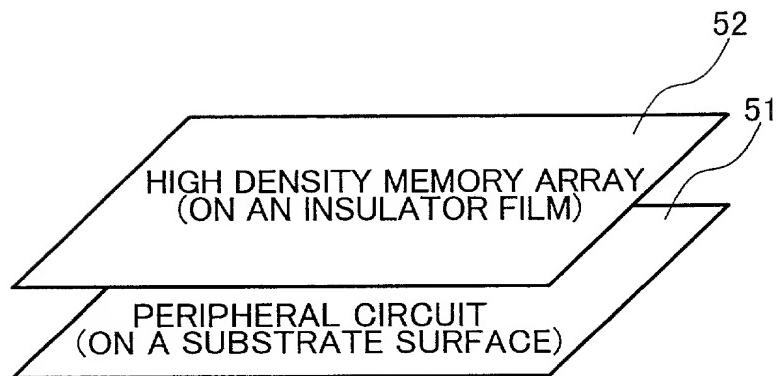


FIG.2b

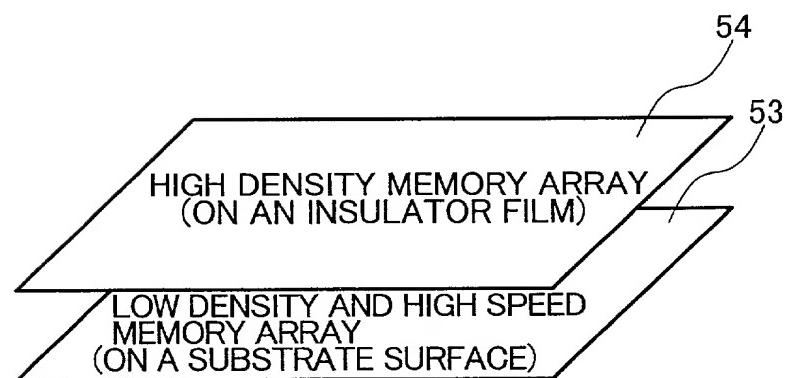


FIG.3

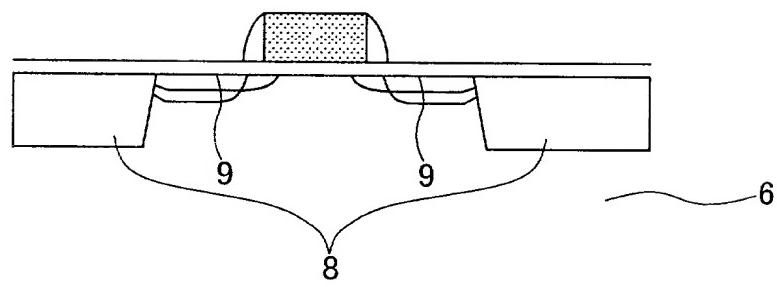


FIG.4

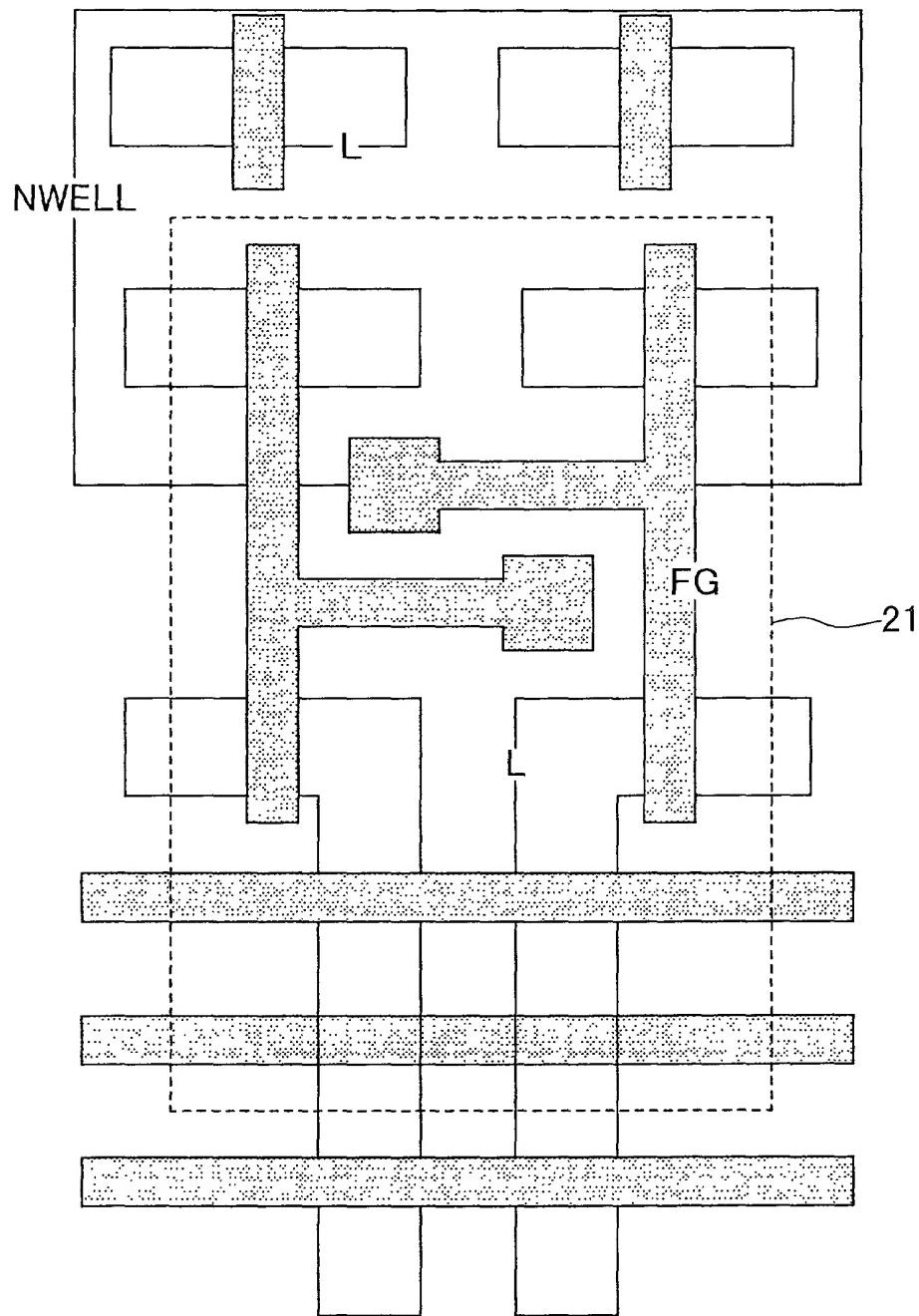


FIG.5

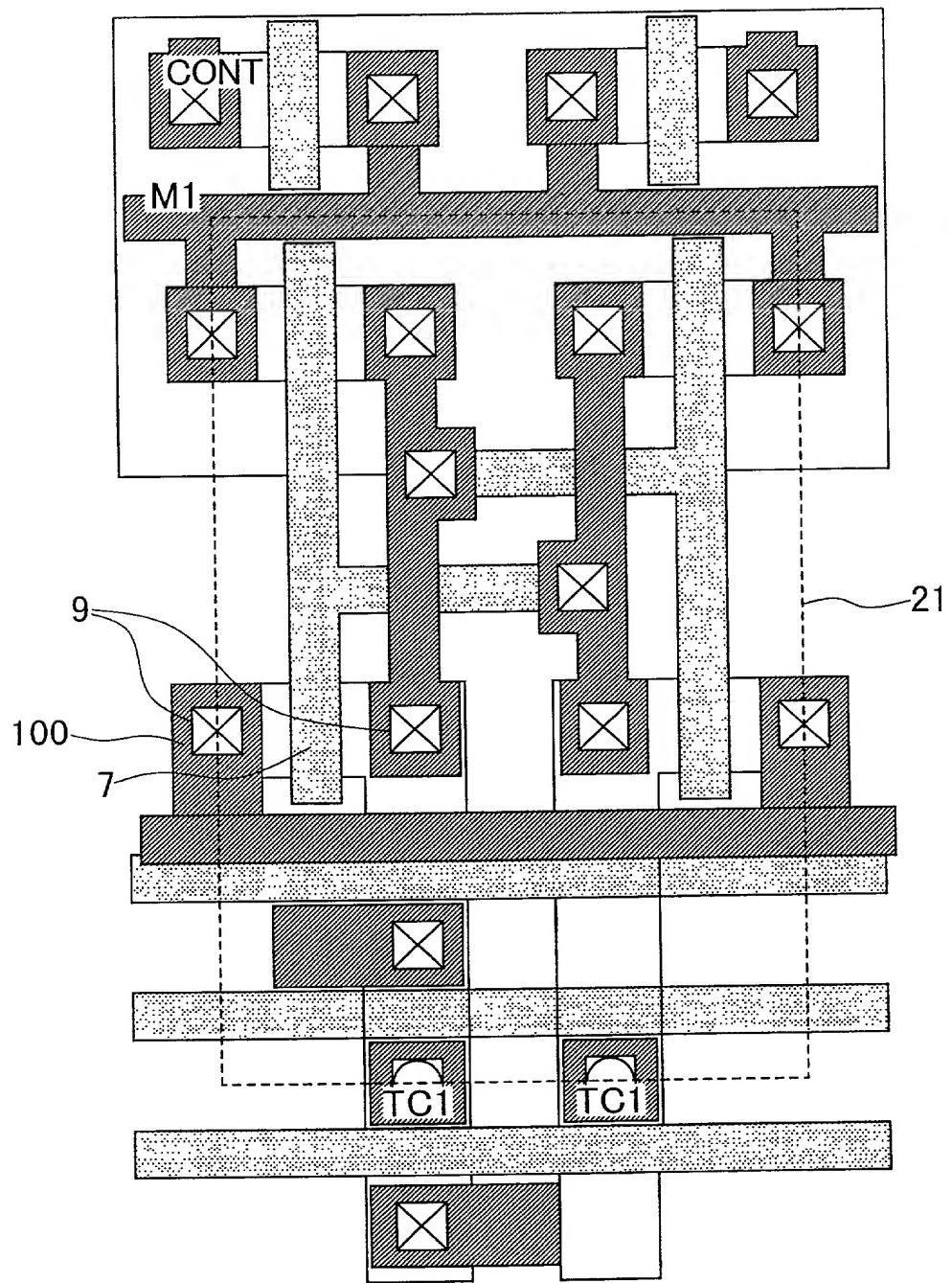


FIG.6

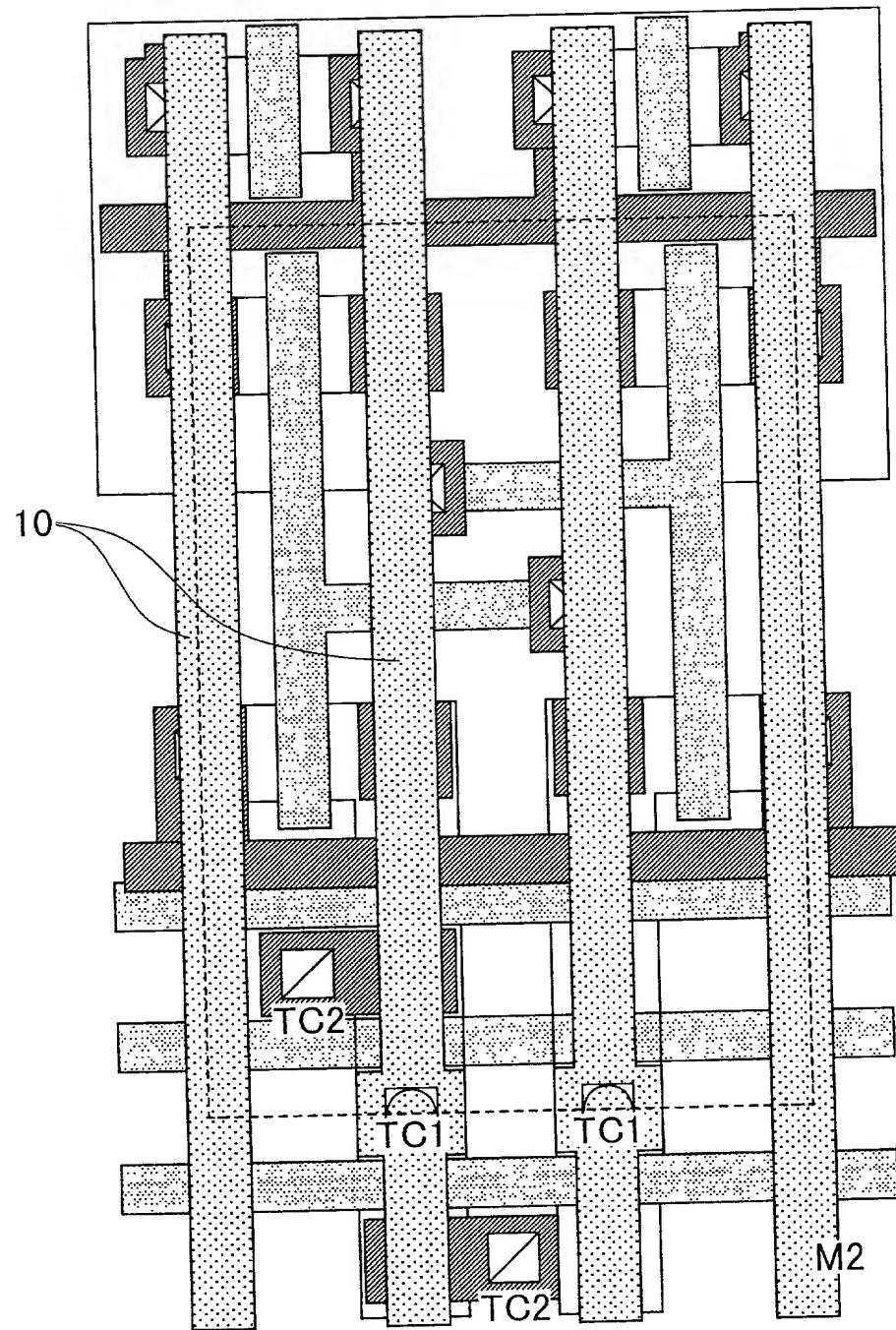


FIG.7

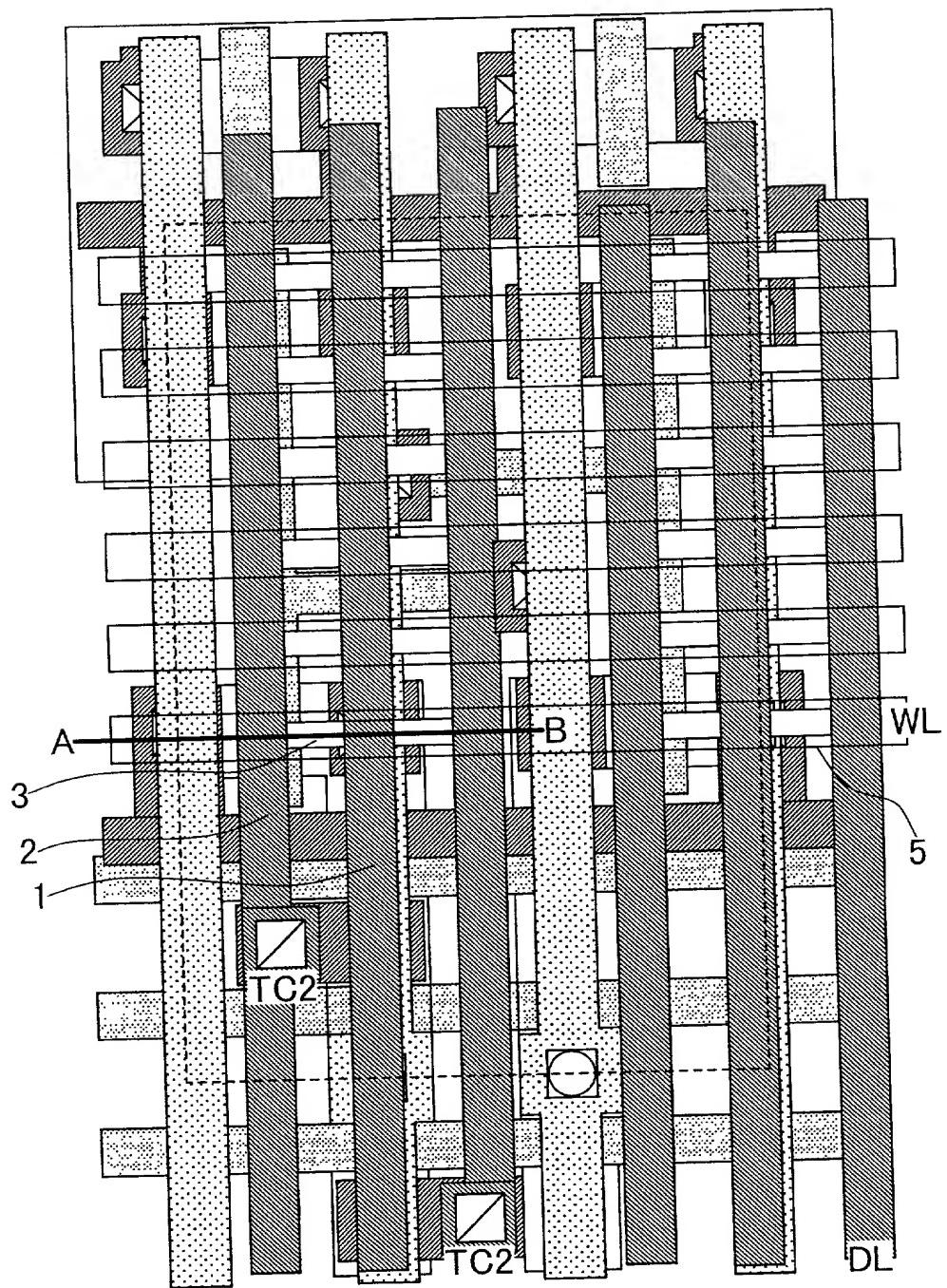


FIG.8

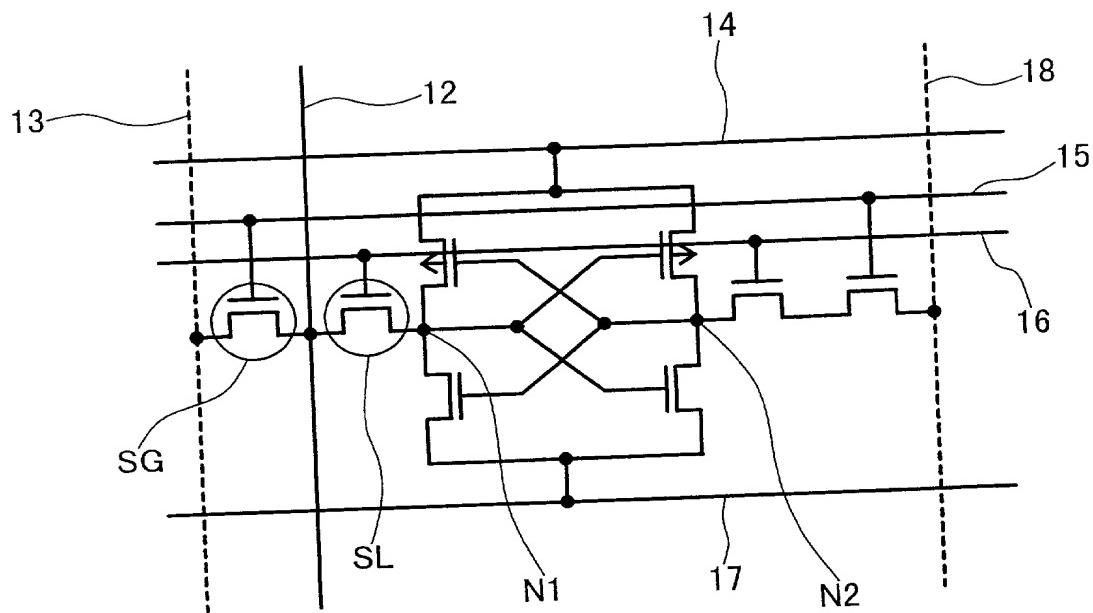


FIG.9

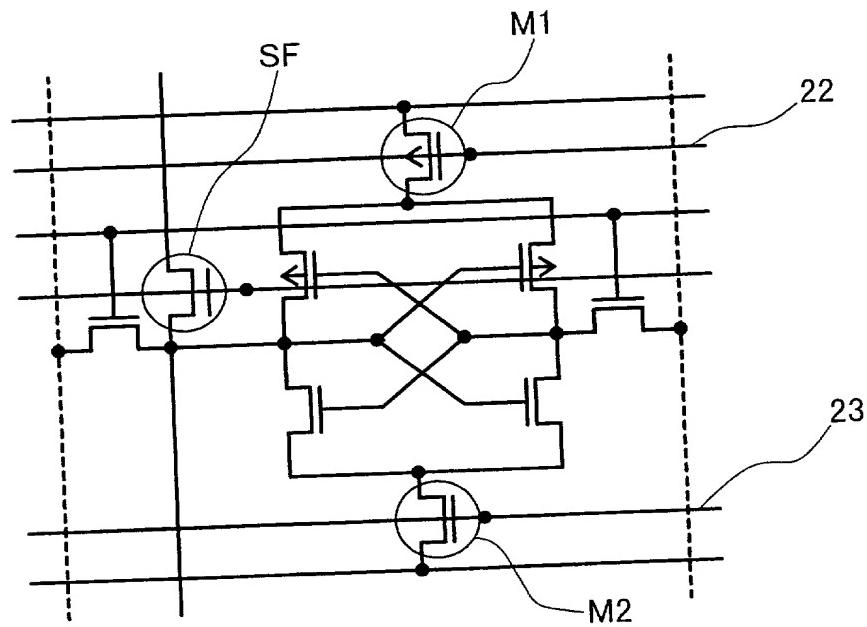


FIG.10

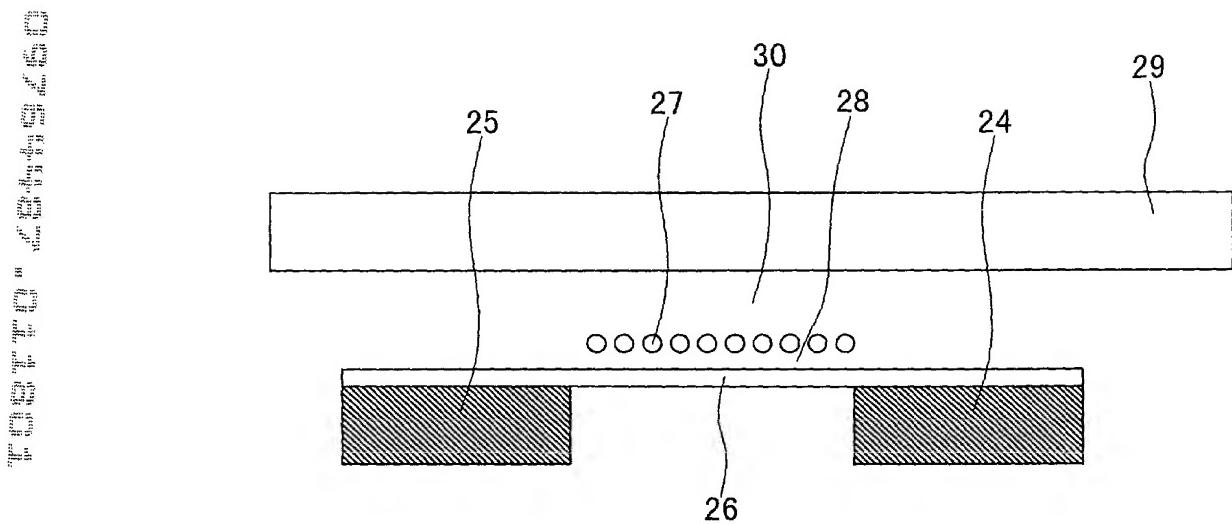


FIG.11

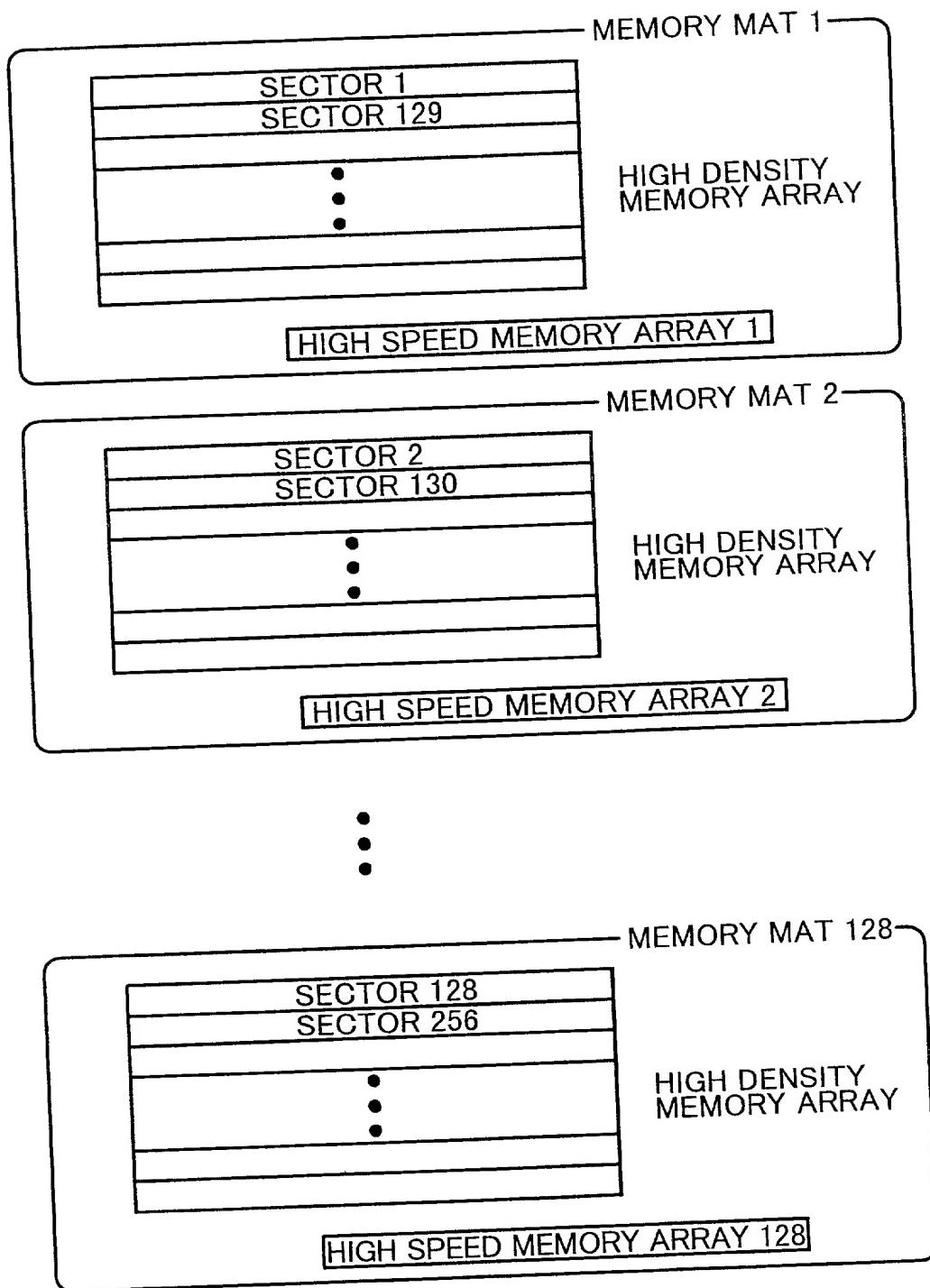


FIG.12

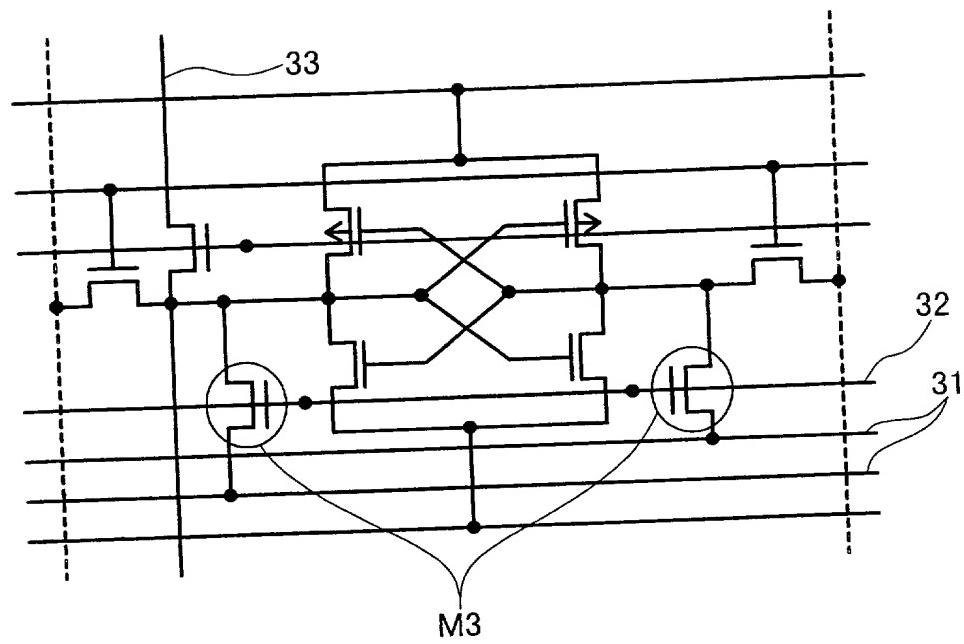


FIG.13

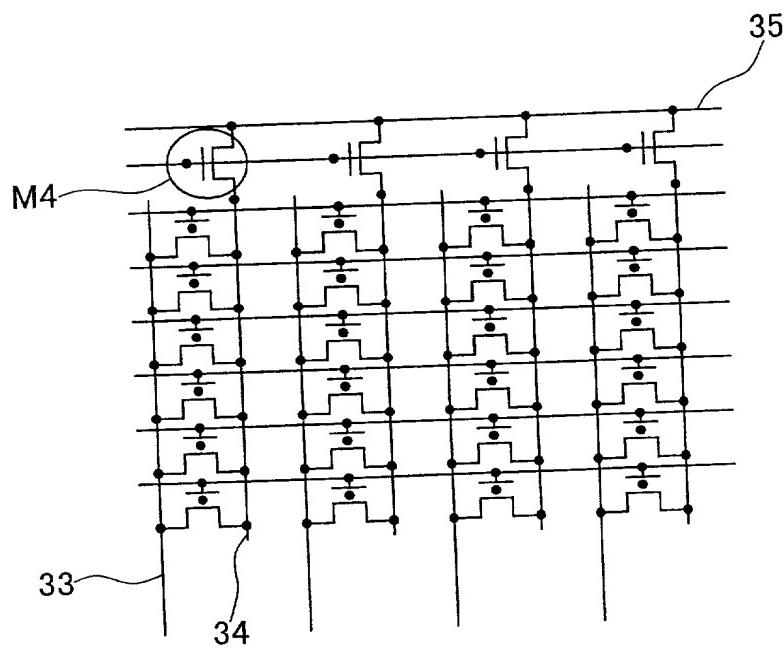


FIG.14

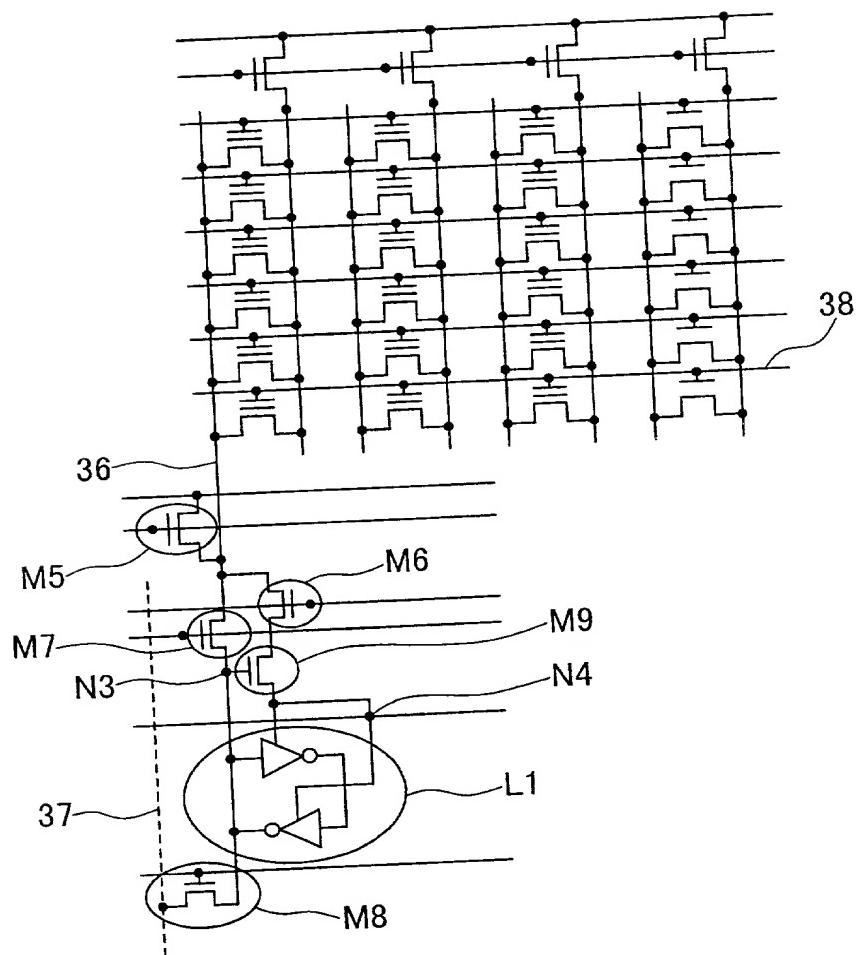


FIG.15a

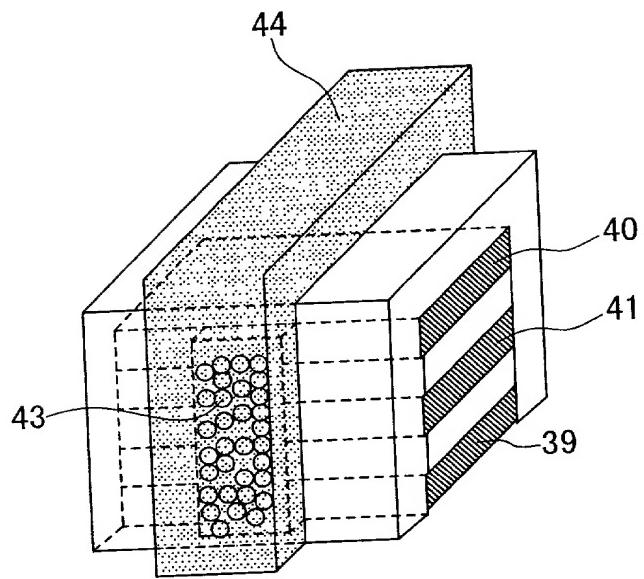


FIG.15b

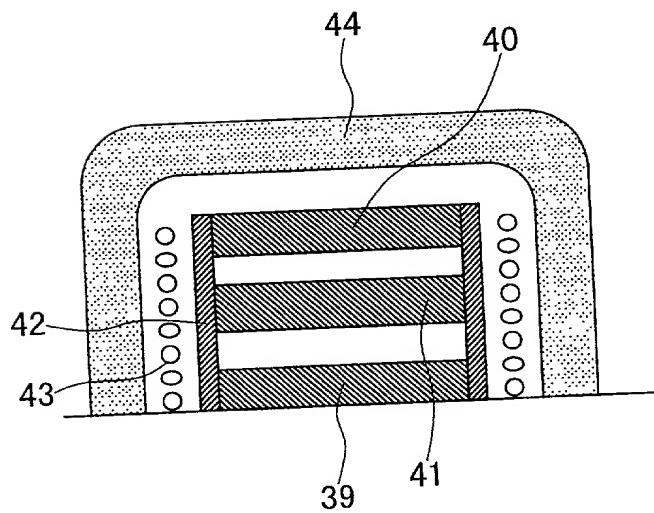


FIG.16

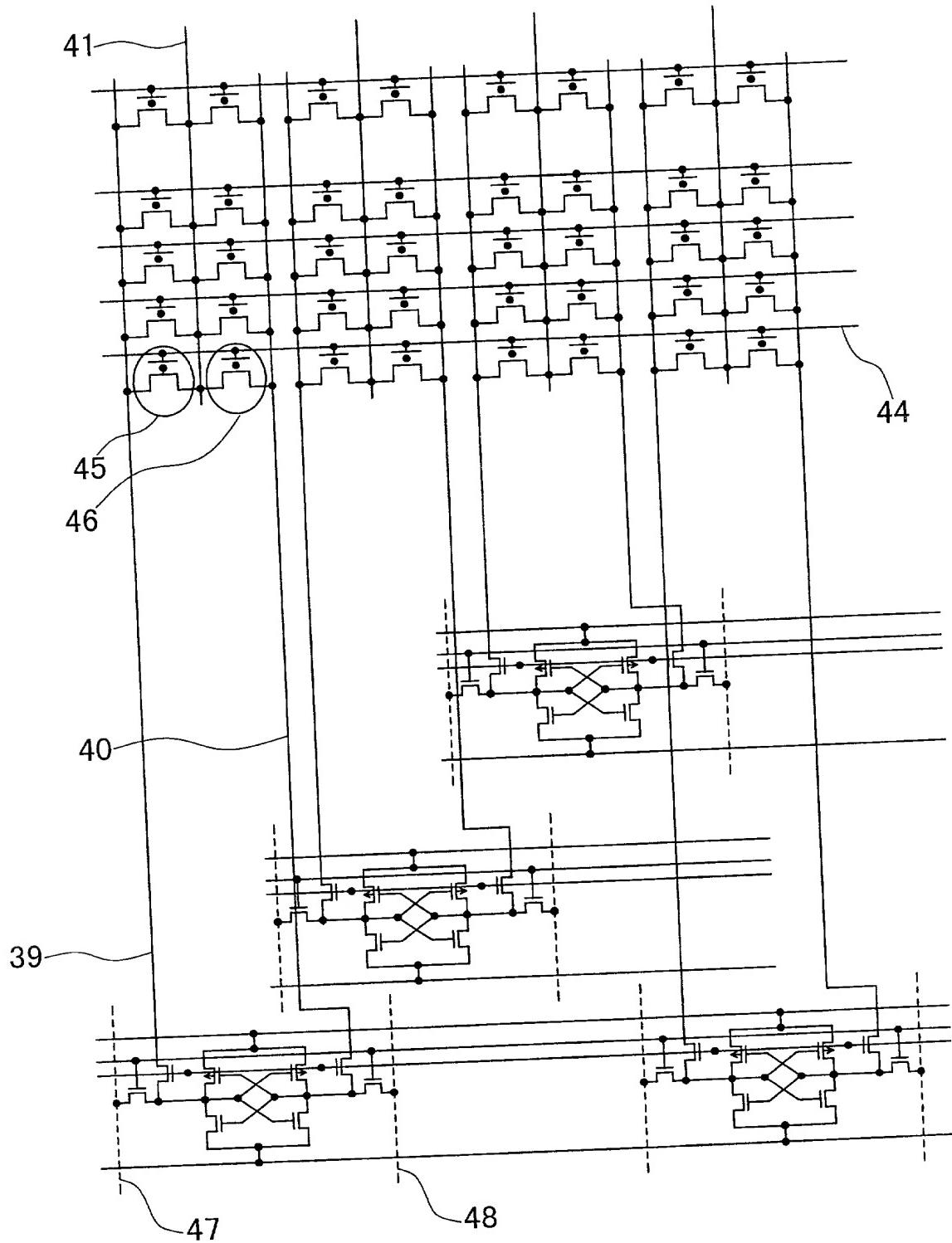


FIG.17

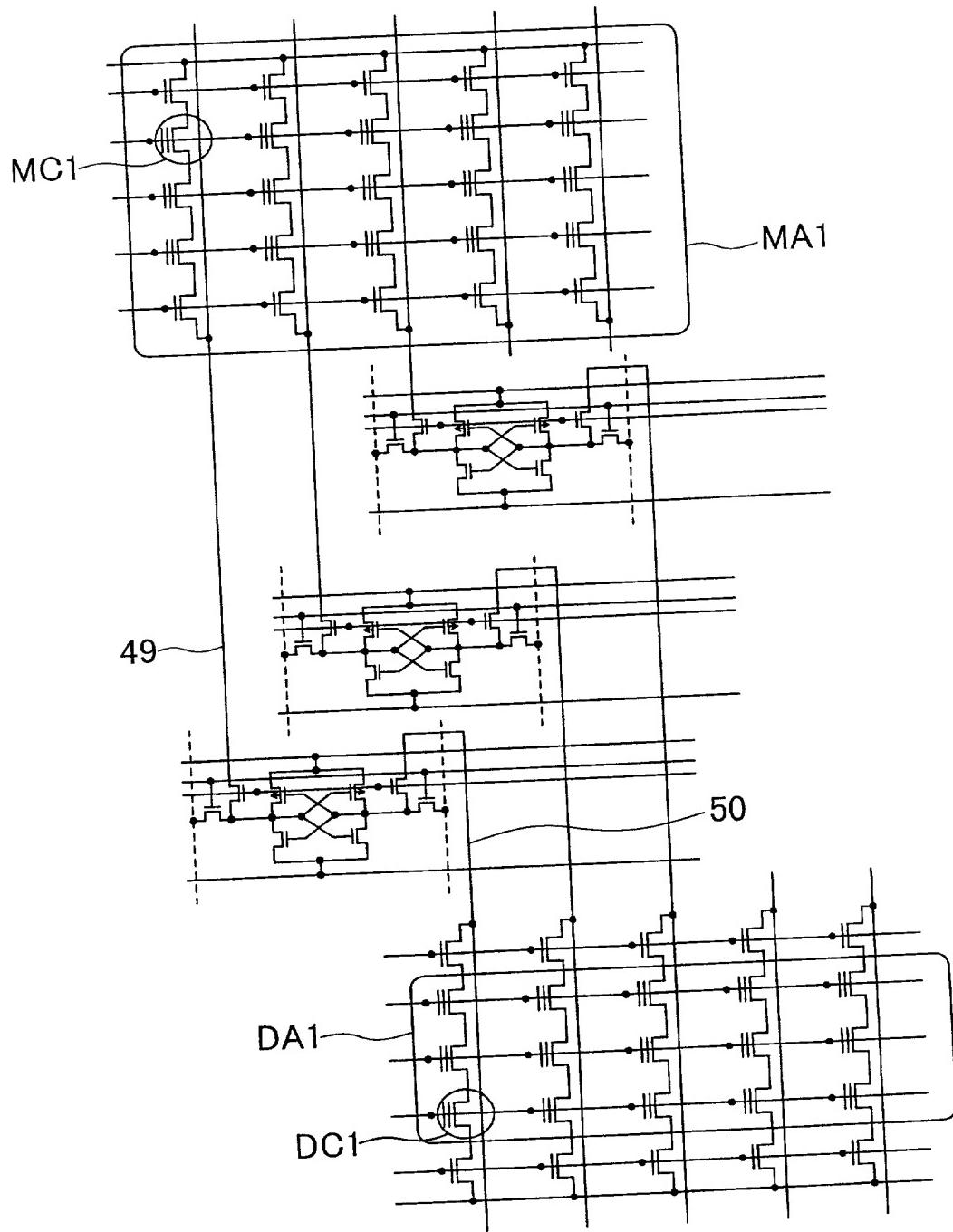


FIG.18a

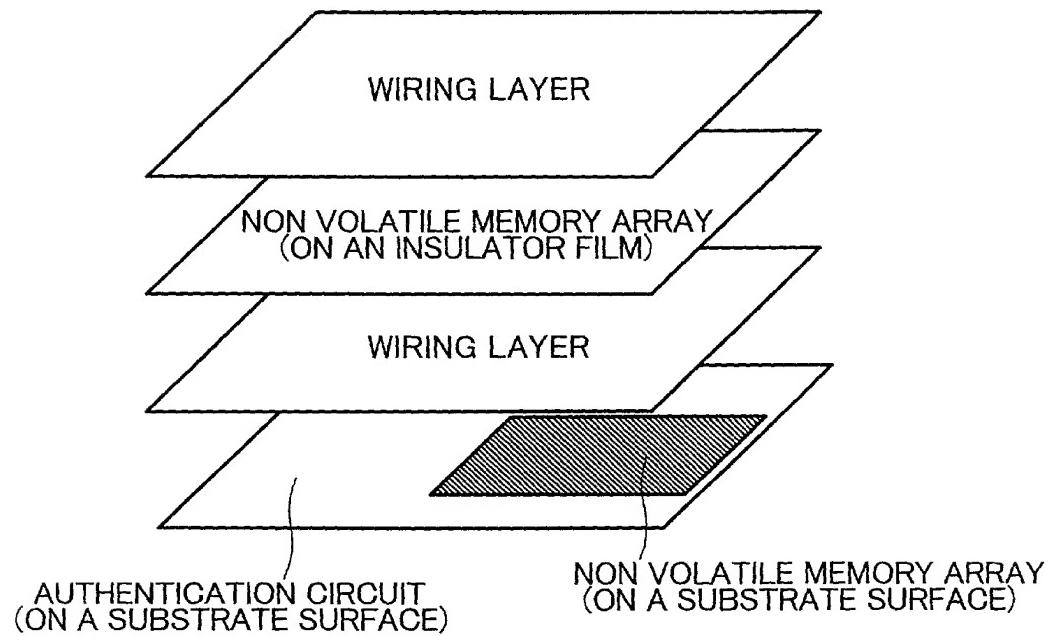


FIG.18b

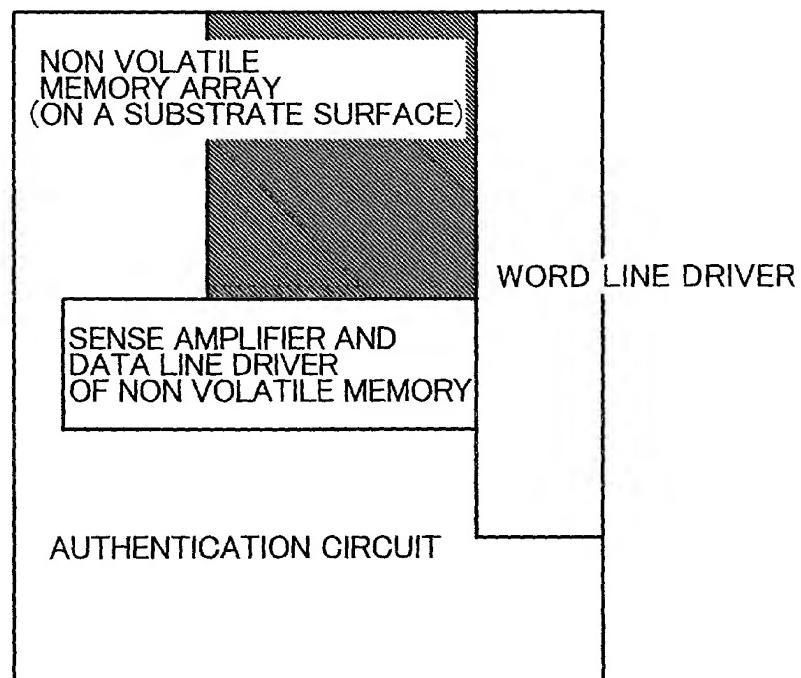


FIG.19a

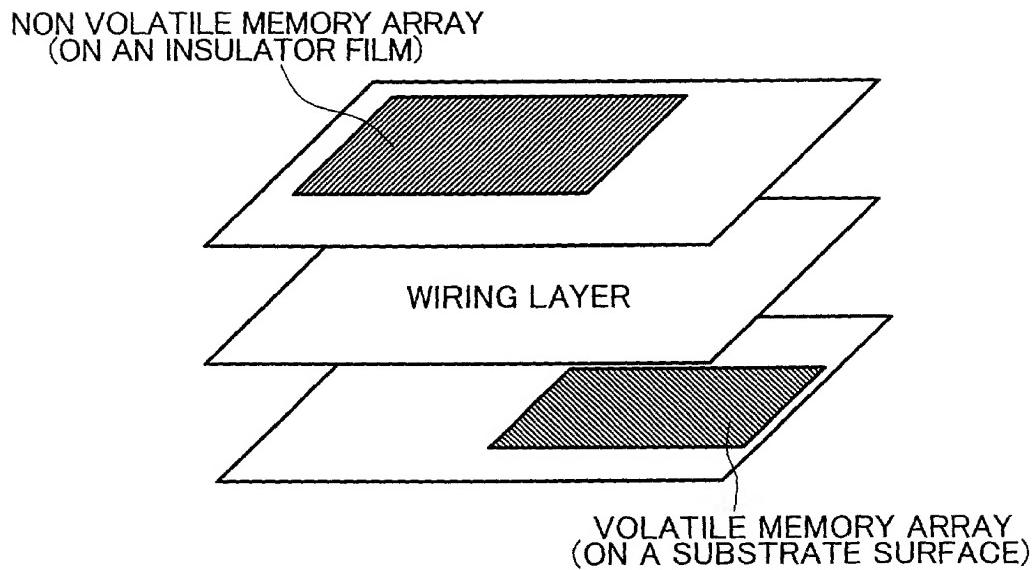


Fig. 19a shows a cross-sectional view of a memory stack. It consists of three layers: a top layer containing a hatched 'NON VOLATILE MEMORY ARRAY (ON AN INSULATOR FILM)', a middle 'WIRING LAYER', and a bottom layer containing a hatched 'VOLATILE MEMORY ARRAY (ON A SUBSTRATE SURFACE)'. The layers are represented by parallel lines.

FIG.19b

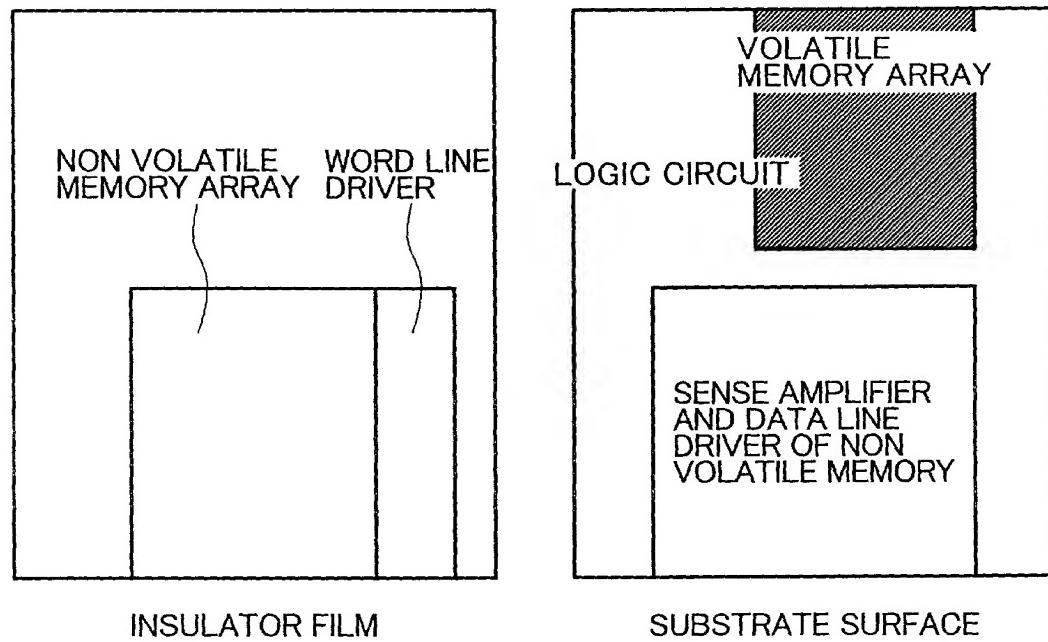


Fig. 19b shows functional blocks. On the 'INSULATOR FILM', there is a 'NON VOLATILE MEMORY ARRAY' and a 'WORD LINE DRIVER'. On the 'SUBSTRATE SURFACE', there is a 'LOGIC CIRCUIT' and a 'SENSE AMPLIFIER AND DATA LINE DRIVER OF NON VOLATILE MEMORY'. The blocks are represented by rectangles with internal hatching.

FIG.20

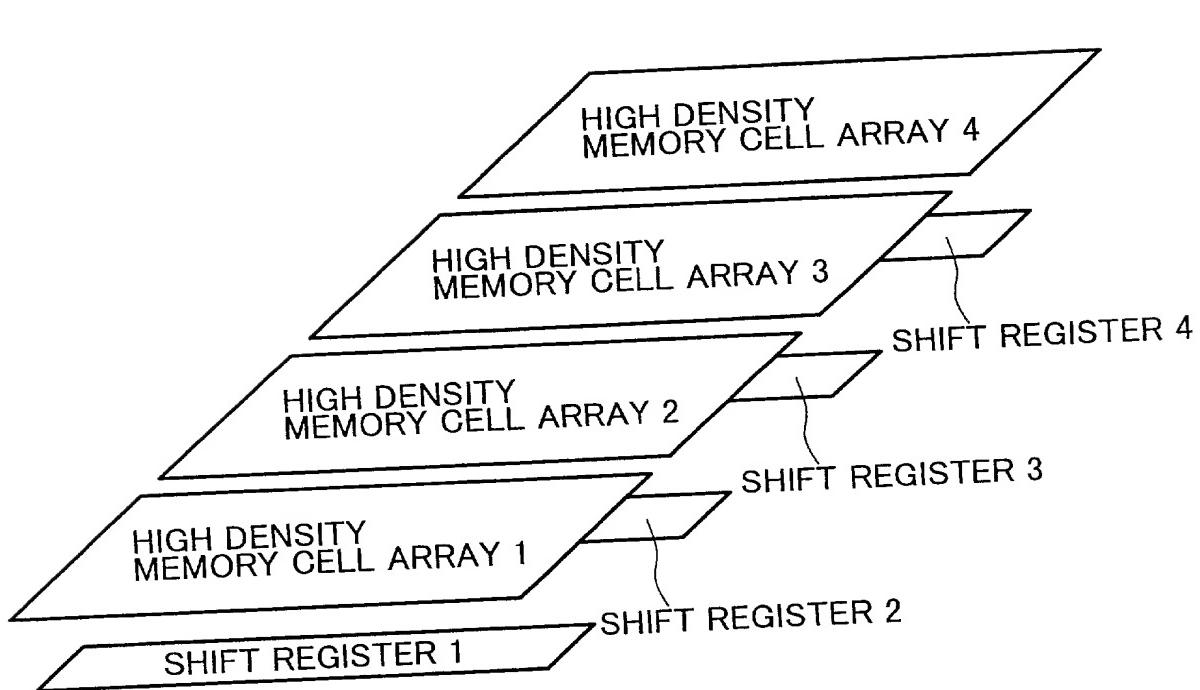


FIG.21

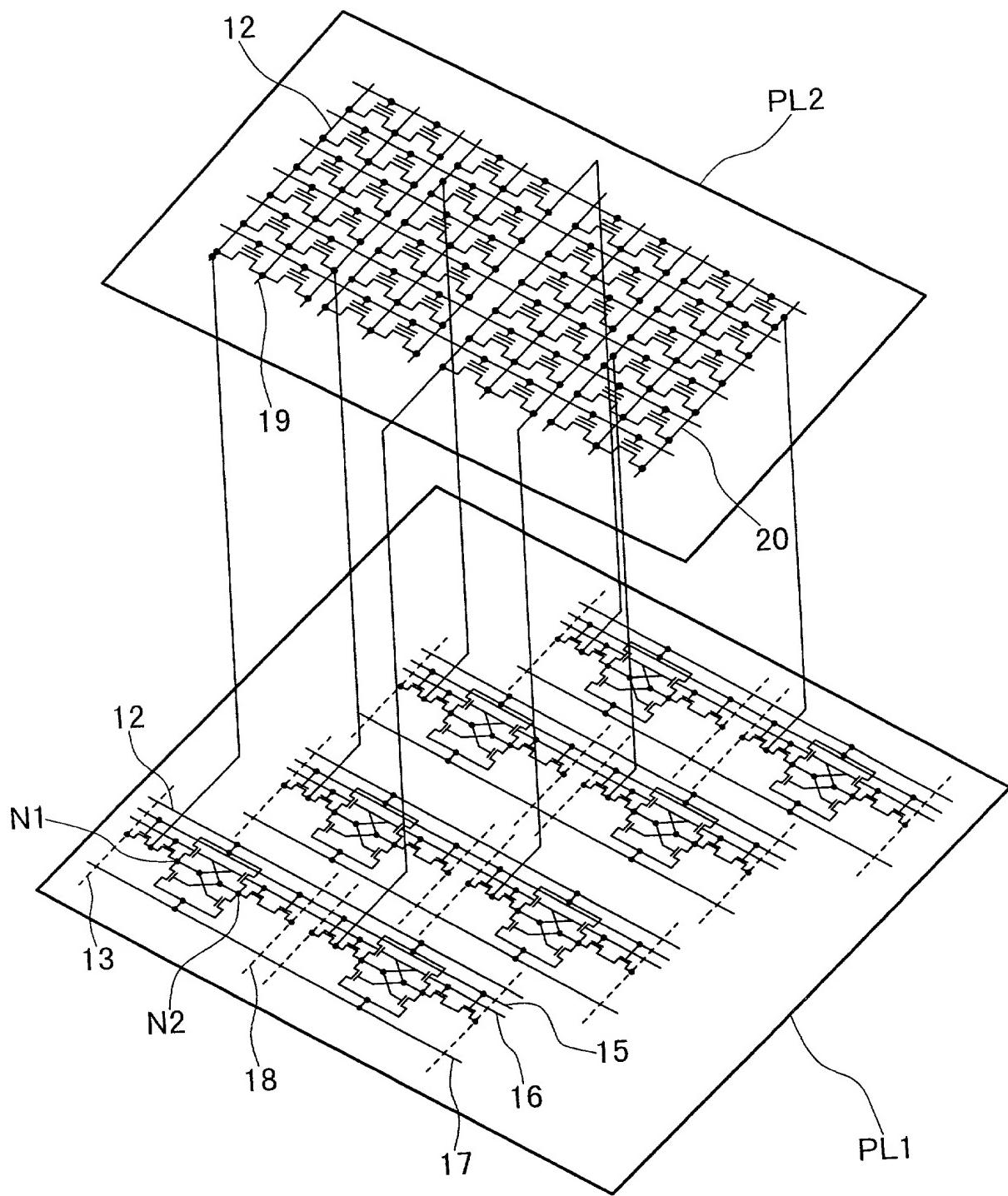


FIG.22

